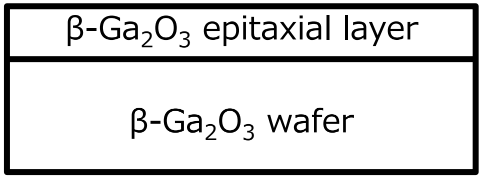
Standard specifications of 10×15 mm^2 β-Ga_2O_3 epitaxial wafer (by MBE)

Epitaxial layer

Items	Specifications	
Dopant	Si (n-type)	Undoped (semi-insulating)
Doping concentration（cm^{-3}） *Selectable within the specified range.	Specify a value between 1×10^{17} and 2×10^{18}	-
Thickness（μm） *Selectable in 1 μm increments.	Specify a value between 0.1 and 0.5	

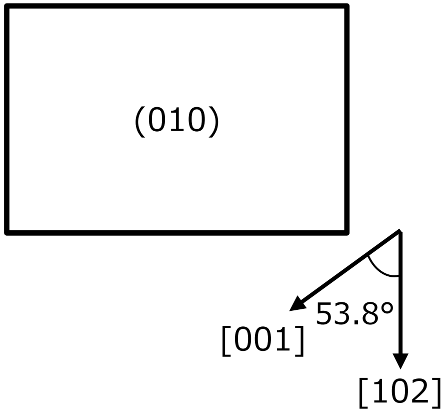

β-Ga_2O_3 epitaxial layer

β-Ga_2O_3 wafer

Cross section of β-Ga_2O_3 epitaxial wafer

Wafer

Items	Specifications	
Dopant	Sn (n-type)	Fe (semi-insulating)
Doping concentration（cm^{-3}）	Using the range of $1–9\times10^{18}$	-
Resistivity（Ω·cm）	-	$\geq 10^{10}$
Orientation	(010)	
Size（mm^2）	10×15	
Thickness（mm）	0.5	
XRD FWHM（arcsec）	≤ 150	
Off set angle（degree）	0 ± 1	



Orientation

Remarks

1 These products must be used for research and development purposes only.

2 The substrates must not be used as a seed crystal.

3 The specifications are subject to change without notice.

Novel Crystal Technology, Inc.

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